OptiMOS™ Power-Transistor

Features

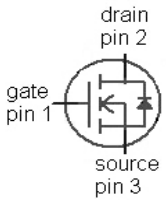
- For fast switching converters and sync. rectification
- N-channel enhancement - logic level
- 175 °C operating temperature
- Avalanche rated
- Pb-free lead plating, RoHS compliant
- Halogen-free according to IEC61249-2-21

RoHS Halogen-Free

Product Summary

V_{DS}	60	V
$R_{DS(on),max\ SMD\ version}$	8.2	mΩ
I_D	80	A

Type	IPB085N06L G	IPP085N06L G
		
Package	P-TO263-3-2	P-TO220-3-1
Marking	085N06L	085N06L



Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	**Symbol**	**Conditions**	**Value**	**Unit**
Continuous drain current	I_D	T_C=25 °C[1)]	80	A
		T_C=100 °C	76	
Pulsed drain current	$I_{D,pulse}$	T_C=25 °C[2)]	320	
Avalanche energy, single pulse	E_{AS}	I_D=80 A, R_{GS}=25 Ω	370	mJ
Reverse diode dv/dt	dv/dt	I_D=80 A, V_{DS}=48 V, di/dt=200 A/µs, $T_{j,max}$=175 °C	6	kV/µs
Gate source voltage	V_{GS}		±20	V
Power dissipation	P_{tot}	T_C=25 °C	188	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

[1)] Current is limited by bondwire; with an R_{thJC}=0.8 K/W the chip is able to carry 97 A.

[2)] See figure 3

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - case	R_{thJC}		-	-	0.8	K/W
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	62	
		6 cm^2 cooling area[3)]	-	-	40	
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=1 mA	60	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=125 µA	1.2	1.6	2	
Zero gate voltage drain current	I_{DSS}	V_{DS}=60 V, V_{GS}=0 V, T_j=25 °C	-	0.01	1	µA
		V_{DS}=60 V, V_{GS}=0 V, T_j=125 °C	-	1	100	
Gate-source leakage current	I_{GSS}	V_{GS}=20 V, V_{DS}=60 V	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=80 A	-	7.0	8.5	mΩ
		V_{GS}=4.5 V, I_D=53 A	-	8.7	12	
		V_{GS}=10 V, I_D=80 A, SMD version		6.7	8.2	
		V_{GS}=4.5 V, I_D=53 A, SMD version		8.4	11.7	
Gate resistance	R_G		-	2.3	-	Ω
Transconductance	g_{fs}	$\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, I_D=80 A	54	107	-	S

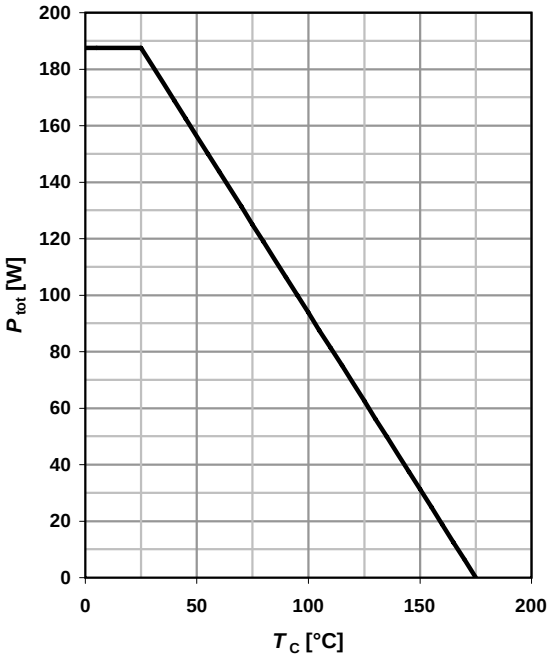
[3)] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=30 V, f=1 MHz	-	2600	3500	pF
Output capacitance	C_{oss}		-	620	820	
Reverse transfer capacitance	C_{rss}		-	150	225	
Turn-on delay time	$t_{d(on)}$	V_{DD}=30 V, V_{GS}=10 V, I_D=80 A, R_G=2.3 Ω	-	10	15	ns
Rise time	t_r		-	19	28	
Turn-off delay time	$t_{d(off)}$		-	53	80	
Fall time	t_f		-	18	27	
Gate Charge Characteristics[4)]						
Gate to source charge	Q_{gs}	V_{DD}=30 V, I_D=80 A, V_{GS}=0 to 10 V	-	10	13	nC
Gate charge at threshold	$Q_{g(th)}$		-	4	6	
Gate to drain charge	Q_{gd}		-	26	39	
Switching charge	Q_{sw}		-	32	47	
Gate charge total	Q_g		-	78	104	
Gate plateau voltage	$V_{plateau}$		-	3.8	-	V
Output charge	Q_{oss}	V_{DD}=30 V, V_{GS}=0 V	-	24	32	
Reverse Diode						
Diode continous forward current	I_S	T_C=25 °C	-	-	80	A
Diode pulse current	$I_{S,pulse}$		-	-	320	
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=80 A, T_j=25 °C	-	0.97	1.3	V
Reverse recovery time	t_{rr}	V_R=30 V, I_F=I_S, di_F/dt=100 A/µs	-	57	70	ns
Reverse recovery charge	Q_{rr}		-	70	90	nC

[4)] See figure 16 for gate charge parameter definition

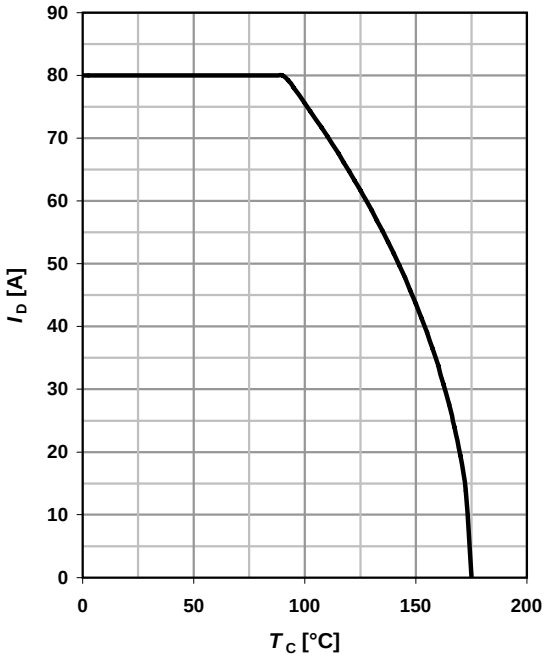
1 Power dissipation

$P_{tot}=f(T_C)$



2 Drain current

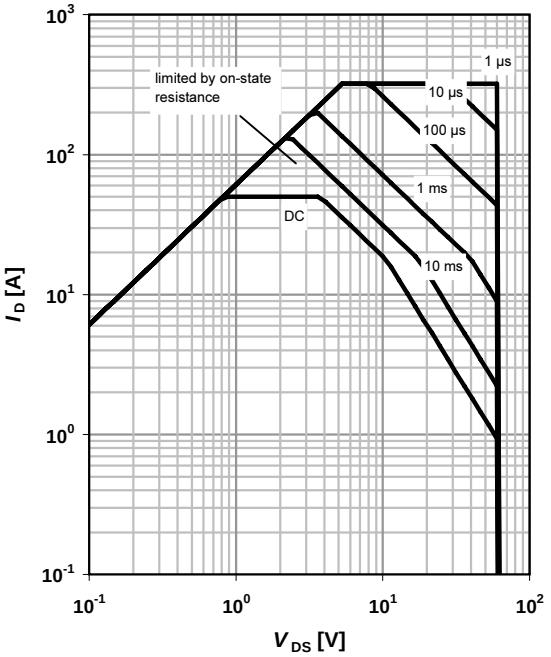
$I_D=f(T_C)$; $V_{GS}\geq 10$ V



3 Safe operating area

$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$

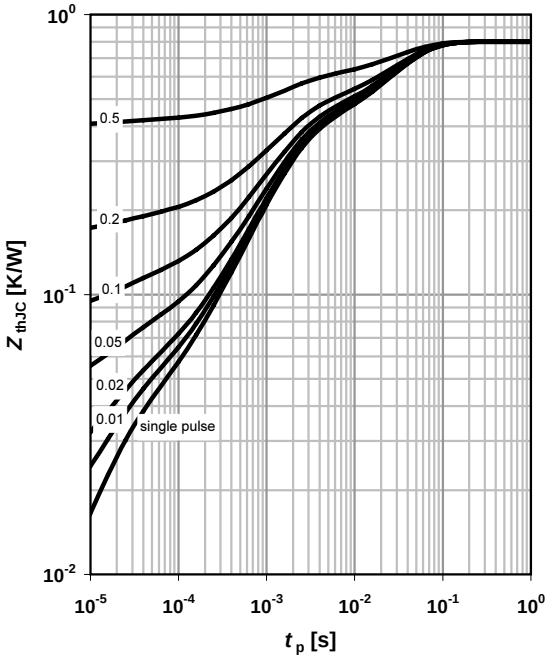
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJC}=f(t_p)$

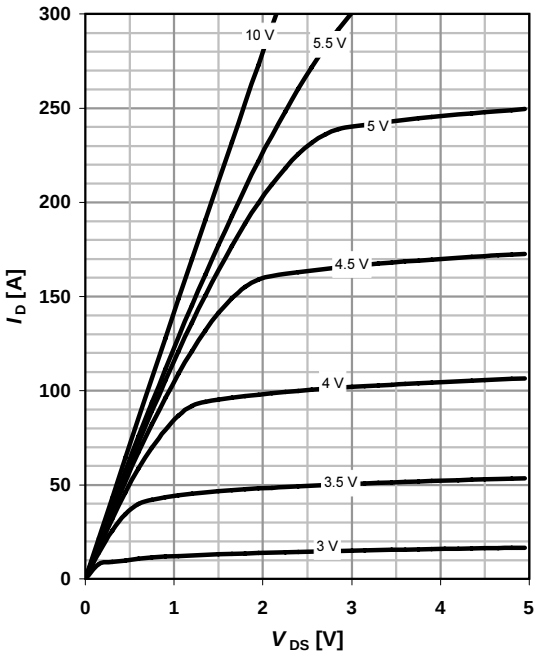
parameter: $D=t_p/T$



5 Typ. output characteristics

$I_D=f(V_{DS})$; T_j=25 °C

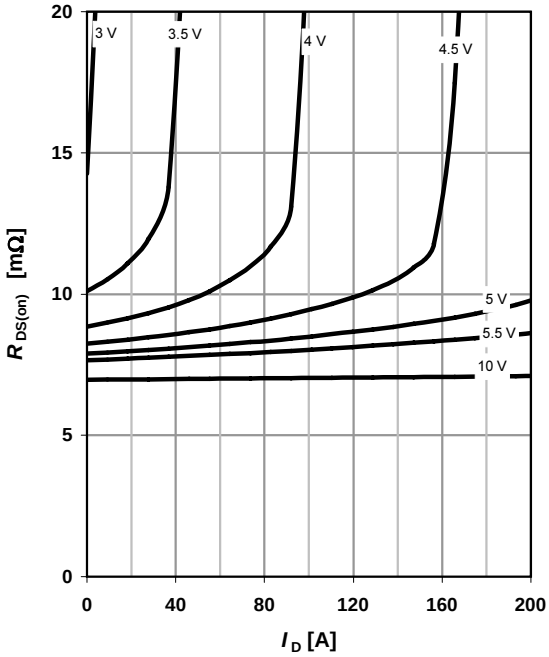
parameter: V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)}=f(I_D)$; T_j=25 °C

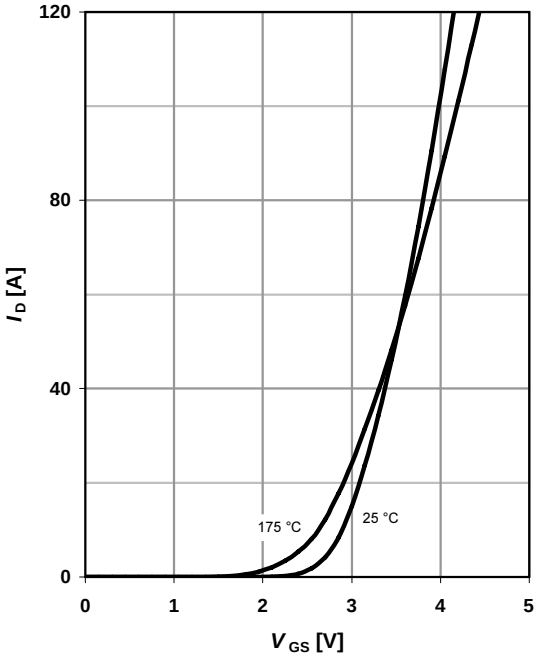
parameter: V_{GS}



7 Typ. transfer characteristics

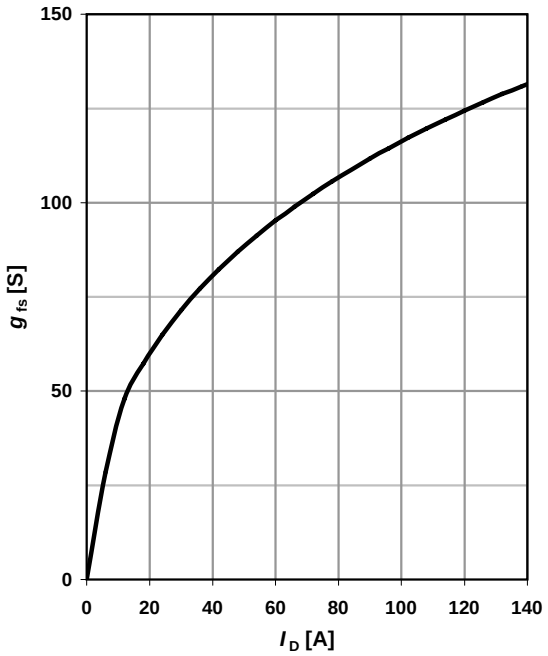
$I_D=f(V_{GS})$; $|V_{DS}|>2|I_D|R_{DS(on)max}$

parameter: T_j



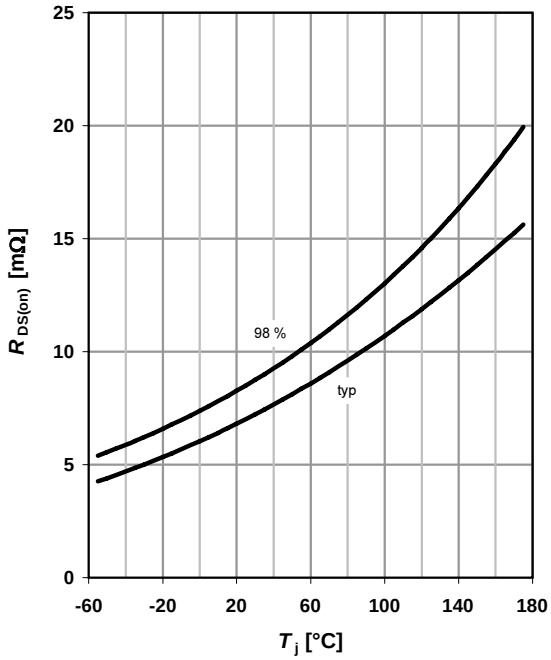
8 Typ. forward transconductance

$g_{fs}=f(I_D)$; T_j=25 °C



9 Drain-source on-state resistance

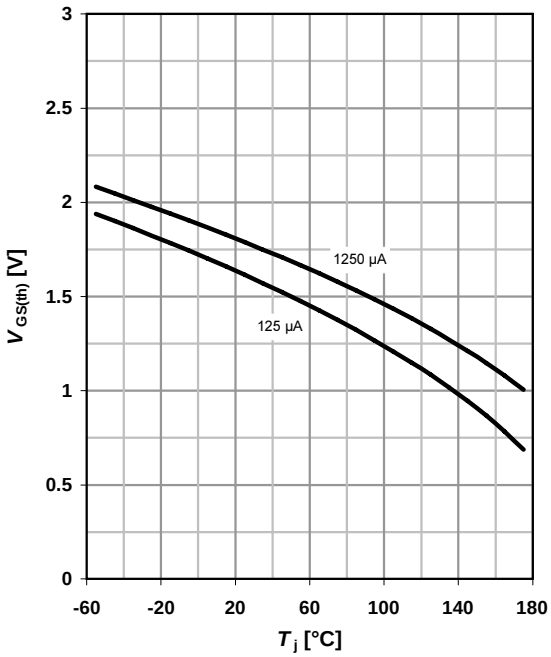
$R_{DS(on)}=f(T_j)$; $I_D=80$ A; $V_{GS}=10$ V



10 Typ. gate threshold voltage

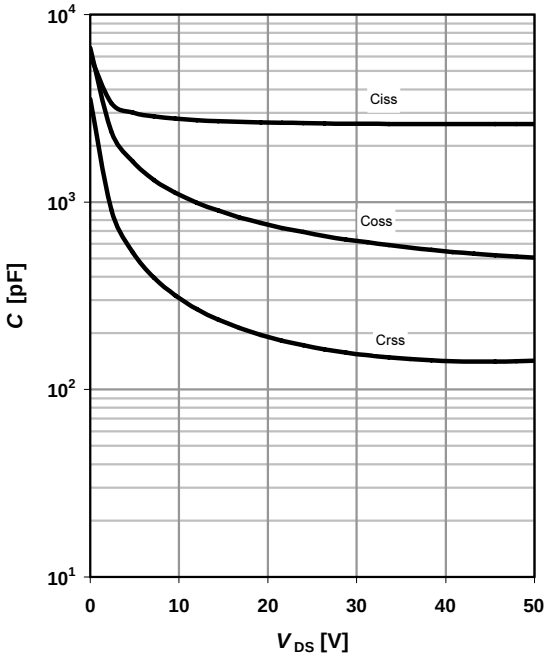
$V_{GS(th)}=f(T_j)$; $V_{GS}=V_{DS}$

parameter: I_D



11 Typ. capacitances

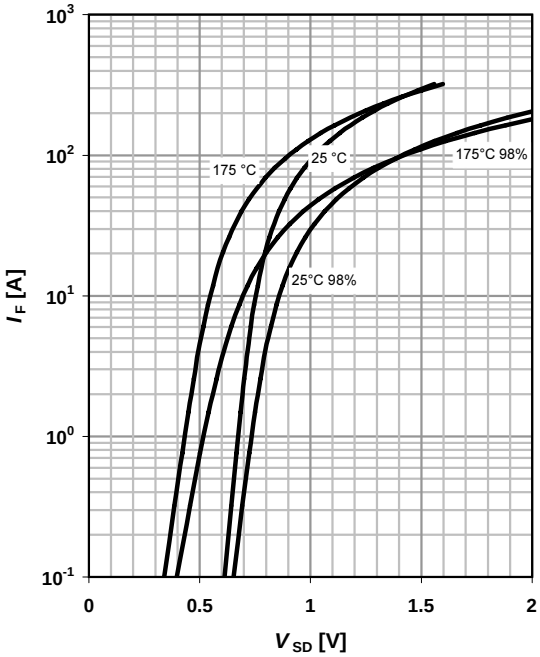
$C=f(V_{DS})$; $V_{GS}=0$ V; $f=1$ MHz



12 Forward characteristics of reverse diode

$I_F=f(V_{SD})$

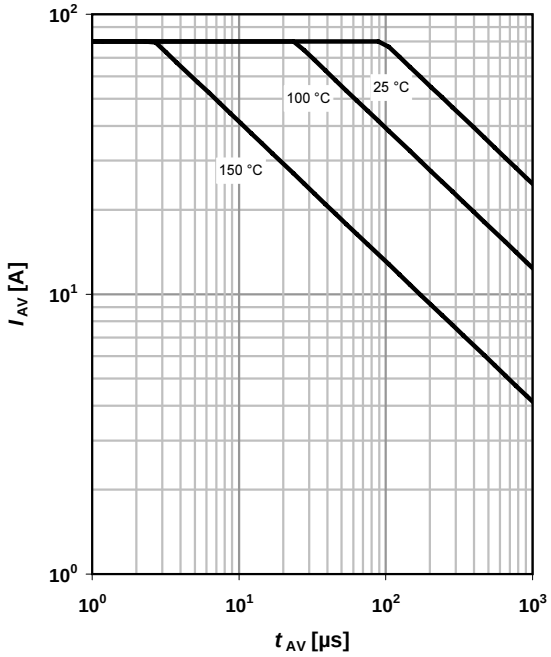
parameter: T_j



13 Avalanche characteristics

I_{AS}=f(t_{AV}); R_{GS}=25 Ω

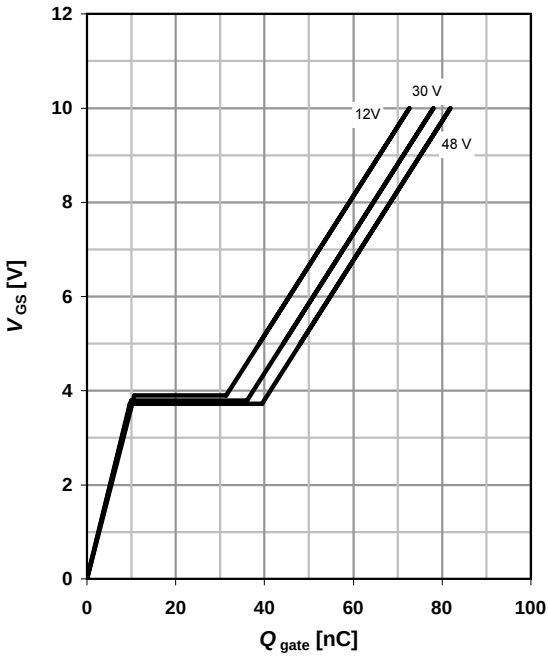
parameter: $T_{j(start)}$



14 Typ. gate charge

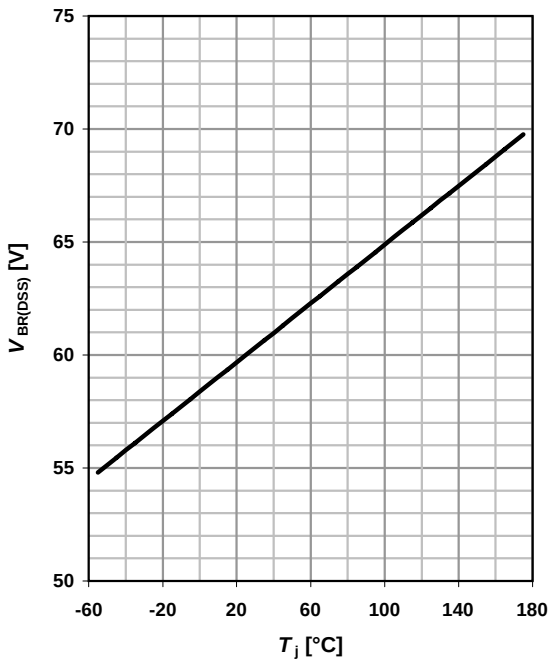
V_{GS}=f(Q_{gate}); I_D=80 A pulsed

parameter: V_{DD}

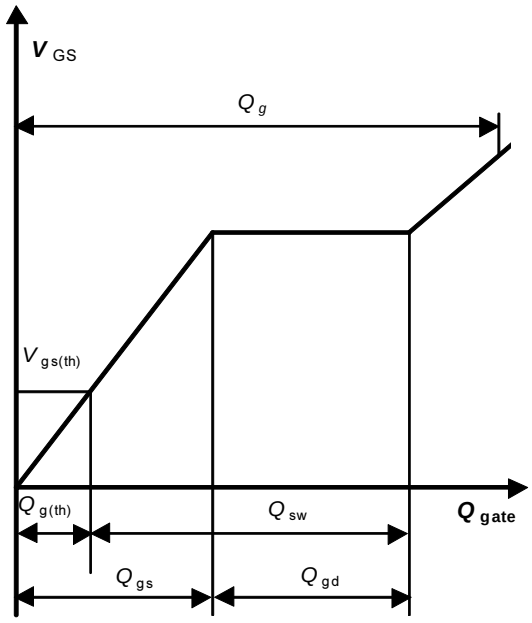


15 Drain-source breakdown voltage

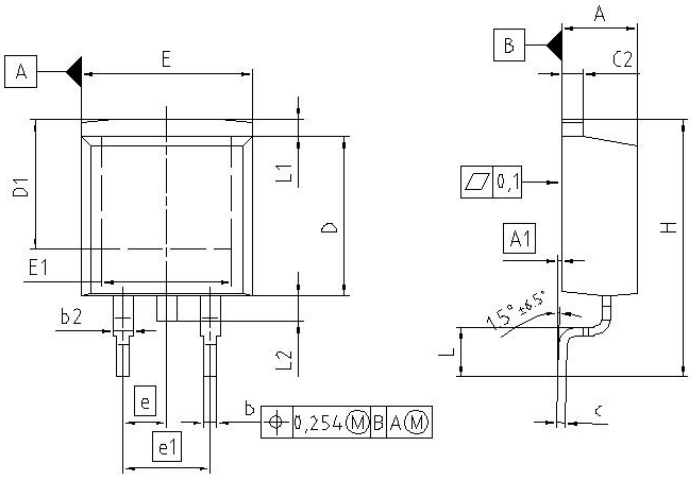
$V_{BR(DSS)}$=f(T_j); I_D=1 mA



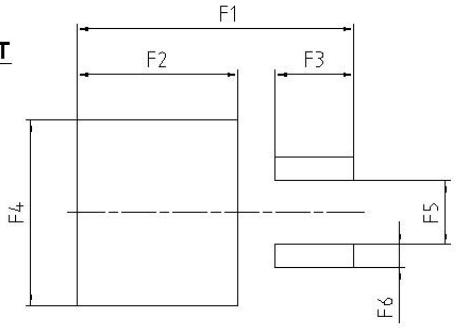
16 Gate charge waveforms



PG-TO-263 (D²-Pak)



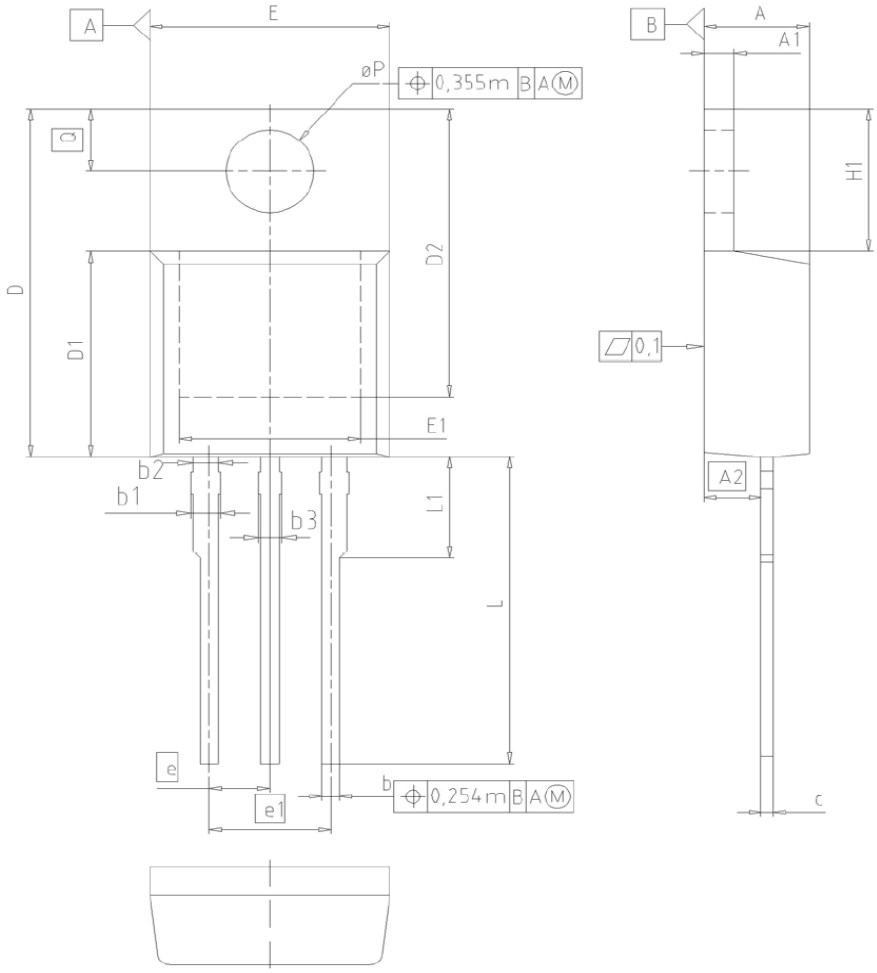
FOOTPRINT



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.300	4.572	0.169	0.180
A1	0.000	0.254	0.000	0.010
b	0.650	0.850	0.026	0.033
b2	0.950	1.321	0.037	0.052
c	0.330	0.650	0.013	0.026
c2	0.170	1.400	0.046	0.055
D	8.509	9.450	0.335	0.372
D1	7.100	-	0.280	-
E	9.800	10.312	0.386	0.406
E1	6.500		0.256	
e	2.540		0.100	
e1	5.080		0.200	
N	2		2	
H	14.605	15.875	0.575	0.625
L	2.200	3.000	0.087	0.118
L1	-	1.600	-	0.063
L2	1.000	1.778	0.039	0.070
F1	16.050	16.250	0.632	0.640
F2	9.300	9.500	0.366	0.374
F3	4.500	4.700	0.177	0.185
F4	10.700	10.900	0.421	0.429
F5	3.630	3.830	0.143	0.151
F6	1.100	1.300	0.043	0.051

REFERENCE JEDEC TO263
SCALE 0 5 5 7.5mm
EUROPEAN PROJECTION
ISSUE DATE 12-02-2006
FILE TO263_2

PG-TO220-3: Outline



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

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